ABSTRACT OF THE DISCLOSURE

CHEMICAL-MECHANICAL-POLISHING SYSTEM AND
CHEMICAL-MECHANICAL-POLISHING METHOD FOR WORKPIECE

A chemical-mechanical-polishing system for polishing a workpiece, such as a wafer, while calculating an estimated polishing rate of the workpiece using a physical model is disclosed. The chemical-mechanical-polishing system is configured to acquire measured polishing physical quantities including a measured polishing rate of a first workpiece and a measured value of torque of a polishing apparatus during or after polishing of the first workpiece; identify the model parameters of the simulation model using the measured polishing physical quantities as variables for identification; and input polishing conditions for a second workpiece into the simulation model to calculate an estimated polishing rate of the second workpiece.

FIG. 1